

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-13. (Canceled)

14. (Currently Amended) A method for manufacturing a semiconductor device comprising:

forming a semiconductor film over a substrate;

blocking end portions of a first laser beam emitted from a laser oscillator by a slit to produce a second laser beam;

producing the second laser beam into a third laser beam by using a condensing lens;

irradiating the semiconductor film with the third laser beam; and

moving the third laser beam relative to the semiconductor film,

wherein an image at the slit and an image on the semiconductor film are in a conjugated relation by the condensing lens.

15. (Currently Amended) A method for manufacturing a semiconductor device comprising:

forming a semiconductor film over a substrate;

combining a first laser beam emitted from a first laser oscillator with a second laser beam emitted from a second laser oscillator by a polarizer, the combined laser beam serving as a third laser beam;

blocking end portions of the third laser beam by a slit to produce a fourth laser beam;

producing the fourth laser beam into a fifth laser beam by using a condensing lens;
irradiating the semiconductor film with the fifth laser beam; and
moving the fifth laser beam relative to the semiconductor film,
wherein an image at the slit and an image on the semiconductor film are in a conjugated relation by the condensing lens.

16. (Original) The method for manufacturing a semiconductor device according to Claim 14 or 15,
wherein the condensing lens is two convex cylindrical lenses or a convex spherical lens.

17. (Original) The method for manufacturing a semiconductor device according to Claim 14 or 15,
wherein the laser beam is a continuous wave laser beam.

18. (Original) The method for manufacturing a semiconductor device according to Claim 17,
wherein the laser beam is emitted from a laser having a medium of a single-crystal YAG, YVO₄, forsterite (Mg₂SiO₄), YAlO₃, or GdVO₄, or a poly-crystal (ceramic) YAG, Y₂O₃, YVO₄, YAlO₃, or GdVO₄, each of which is doped with one or a plurality of elements selected from the group consisting of Nd, Yb, Cr, Ti, Ho, Er, Tm, and Ta as dopant, a solid-state laser such as an alexandrite laser or a Ti:sapphire laser, a gas laser such as an Ar ion laser or a Kr ion laser, or a semiconductor laser such as a GaN laser, a GaAs laser, or an InAs laser.

19. (Original) The method for manufacturing a semiconductor device according to Claim 14 or 15,

wherein the laser beam has a pulse width of femtoseconds.

20. (Original) The method for manufacturing a semiconductor device according to Claim 19,

wherein the laser beam is emitted from a Ti:sapphire laser, a chromium-forsterite laser, or a Yb:YAG laser.

21. (Original) The method for manufacturing a semiconductor device according to Claim 14 or 15,

wherein the laser beam is a pulsed laser beam with a repetition rate of 10 MHz or more.

22. (Original) The method for manufacturing a semiconductor device according to Claim 21,

wherein the laser beam is emitted from a laser having a medium of a single-crystal YAG, YVO₄, forsterite (Mg₂SiO₄), YAlO₃, or GdVO₄, or a poly-crystal (ceramic) YAG, Y₂O₃, YVO₄, YAlO₃, or GdVO₄, each of which is doped with one or a plurality of elements selected from the group consisting of Nd, Yb, Cr, Ti, Ho, Er, Tm, and Ta as dopant, an Ar ion laser, or a Ti:sapphire laser.

23. (Original) The method for manufacturing a semiconductor device according to Claim 14 or 15,

wherein a width of a microcrystal region to a laser irradiation region formed by the irradiation ranges from 1 to 20 μm.

24. (Original) The method for manufacturing a semiconductor device according to Claim 14 or 15,

wherein the slit has a blocking plate which is opened and closed.

25. (Canceled)

26. (Currently Amended) A laser irradiation method comprising:
blocking end portions of a first laser beam emitted from a laser oscillator by a slit
to produce a second laser beam;
producing the second laser beam into a third laser beam by using a condensing
lens;
irradiating an irradiation surface with the third laser beam; and
moving the third laser beam relative to the irradiation surface,
wherein an image at the slit and an image on the irradiation surface are in a
conjugated relation by the condensing lens.

27. (Currently Amended) A laser irradiation method comprising:
combining a first laser beam emitted from a first laser oscillator with a second
laser beam emitted from a second laser oscillator by a polarizer, the combined laser
beam serving as a third laser beam;
blocking end portions of the third laser beam by a slit to produce a fourth laser
beam;
producing the fourth laser beam into a fifth laser beam by using a condensing
lens;
irradiating an irradiation surface with the fifth laser beam; and
moving the fifth laser beam relative to the irradiation surface,
wherein an image at the slit and an image on the irradiation surface are in a
conjugated relation by the condensing lens.

28. (Original) The laser irradiation method according to Claim 26 or 27,

wherein the condensing lens is two convex cylindrical lenses or a convex spherical lens.

29. (Original) The laser irradiation method according to Claim 26 or 27, wherein the laser beam is a continuous wave laser beam.

30. (Original) The laser irradiation method according to Claim 29, wherein the laser beam is emitted from a laser having a medium of a single-crystal YAG, YVO_4 , forsterite (Mg_2SiO_4), YAlO_3 , or GdVO_4 , or a poly-crystal (ceramic) YAG, Y_2O_3 , YVO_4 , YAlO_3 , or GdVO_4 , each of which is doped with one or a plurality of elements selected from the group consisting of Nd, Yb, Cr, Ti, Ho, Er, Tm, and Ta as dopant, a solid-state laser such as an alexandrite laser or a Ti:sapphire laser, a gas laser such as an Ar ion laser or a Kr ion laser, or a semiconductor laser such as a GaN laser, a GaAs laser, or an InAs laser.

31. (Original) The laser irradiation method according to Claim 26 or 27, wherein the laser beam has a pulse width of femtoseconds.

32. (Original) The laser irradiation method according to Claim 31, wherein the laser beam is emitted from a Ti:sapphire laser, a chromium•forsterite laser, or a Yb:YAG laser.

33. (Original) The laser irradiation method according to Claim 26 or 27, wherein the laser beam is a pulsed laser beam with a repetition rate of 10 MHz or more.

34. (Original) The laser irradiation method according to Claim 33,

wherein the laser beam is emitted from a laser having a medium of a single-crystal YAG, YVO_4 , forsterite (Mg_2SiO_4), YAIO_3 , or GdVO_4 , or a poly-crystal (ceramic) YAG, Y_2O_3 , YVO_4 , YAIO_3 , or GdVO_4 , each of which is doped with one or a plurality of elements selected from the group consisting of Nd, Yb, Cr, Ti, Ho, Er, Tm, and Ta as dopant, an Ar ion laser, or a Ti:sapphire laser.

35. (Original) The laser irradiation method according to Claim 26 or 27, wherein a width of a microcrystal region to a laser irradiation region formed by the laser irradiation apparatus ranges from 1 to 20 μm .

36. (Original) The laser irradiation method according to Claim 26 or 27, wherein the slit has a blocking plate which is opened and closed.

37. (Canceled)

38. (Previously Presented) The method for manufacturing a semiconductor device according to claim 15, wherein the polarizing direction of the first laser beam has been changed by a waveplate.

39. (Previously Presented) The laser irradiation method according to claim 27, wherein the polarizing direction of the first laser beam has been changed by a waveplate.